

# Wide Band GaAs MMIC Amplifier 2.0 - 8.0 GHz

Rev. V6

#### **Features**

- 18 dB Typical Gain
- ± 0.5 dB Typical Broadband Gain Flatness
- Single Bias Supply: +10 V
- DC Decoupled RF Input and Output

### **Description**

MAAM28000 is a wide band. The amplifier. It includes two distributed gain stages to obtain flat gain and a good, 50-ohm input and output impedance match over a very wide bandwidth. The MAAM28000 operates from a single +10 V supply.

The MAAM28000 performs well as a generic IF, driver or buffer amplifier where high gain, excellent linearity and low power consumption are important. Because of its wide bandwidth, the MAAM28000 can be used in numerous commercial and government system applications, such as satellite communications, RLL, EW and radar.

MAAM28000 is manufactured The in-house using a reliable, 0.5-micron, GaAs MESFET process. This product is 100% RF tested to ensure compliance to performance specifications.

## Ordering Information

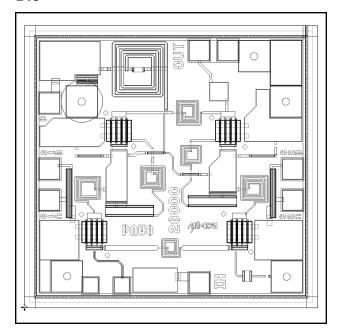
Part Number	Package		
MAAM28000	Die		

# Absolute Maximum Ratings 1

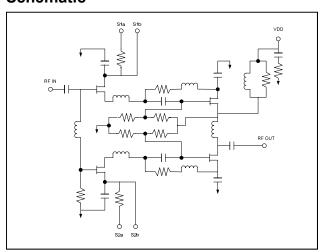
Parameter	Absolute Maximum		
Voltage	+14 V		
Input Power	+20 dBm		
Operating Temperature	-55°C to +125°C		
Storage Temperature	-65°C to +150°C		

1. Exceeding any one or combination of these limits may cause permanent damage to this device.

#### Die



#### **Schematic**



- India Tel: +91.80.43537383 Visit www.macomtech.com for additional data sheets and product information.
- China Tel: +86.21.2407.1588

changes to the product(s) or information contained herein without notice.



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### **Electrical Specifications:**

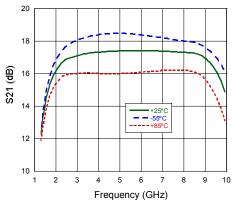
 $T_A = 25^{\circ}C$ ,  $Z_0 = 50 \Omega$ ,  $V_{DD} = +10 \ VDC$ ,  $I_{DD} = 60 \ mA \ Typ.$ , 100 mA Max.

Parameter	Test Conditions	Units	Min.	Тур.	Max.
Gain <sup>2</sup>	_	dB	16.0	18.0	_
Gain Flatness	_	dB		± 0.5	
Noise Figure <sup>2</sup>	2.0 - 4.0 GHz 4.0 - 6.0 GHz 6.0 - 8.0 GHz	dB dB dB	_ _ _	6.0 4.5 4.0	7.5 6.0 5.5
Input VSWR Output VSWR	_	Ratio Ratio		1.7:1 1.3:1	_ _
Output Power at 1 dB Gain Compression	_	dBm	_	14	_
Third Order Intercept	_	dBm	_	24	_
Reverse Isolation	<del>-</del>	dB	_	40	_
Impedance	<del>-</del>	Ω	_	50	_

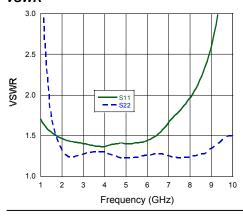
<sup>2. 100%</sup> on-wafer tested.

# **Typical Performance Curves**

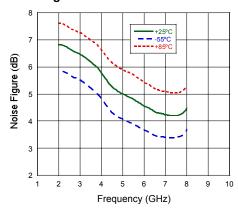
#### Gain



### **VSWR**



#### Noise Figure



Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

**ADVANCED**: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology

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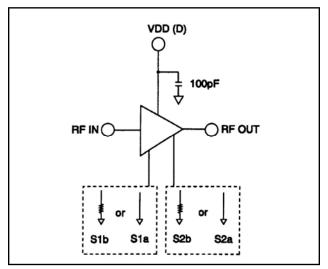
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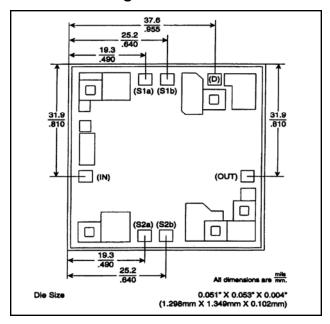
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# Typical Bias Configuration 3,4



- 3. Nominal bias is obtained with on-chip resistors by grounding pads S1a and S2a.
- 4. Optional biasing can be obtained with off-chip resistors bonded from pads S1b and S2b to ground. Adjusting the bias can customize the performance to suit special requirements.

### **Outline Drawing**



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#### **Handling Procedures**

Permanent damage to the MAAM28000 may occur if the following precautions are not adhered to:

- A. Cleanliness The MAAM28000 should be handled in a clean environment. DO NOT attempt to clean assembly after the MAAM28000 is installed.
- B. Static Sensitivity All die handling equipment and personnel should comply with DOD-STD-1686 Class I.
- C. Transients Avoid instrument and power supply transients while bias is connected to the MAAM28000. Use shielded signal and bias cables to minimize inductive pick-up.
- D. General Handling DO NOT touch the surface of the die. It is recommended that the MAAM28000 die be handled along the long side with a sharp pair of tweezers.

#### Mounting

The MAAM28000 is back-metalized with Pd/Ni/Au (100/1, 000/30,000Å) metallization. It can be diemounted using Au/Sn eutectic preforms or a thermally and electrically conductive epoxy. The attachment surface should be clean and flat.

#### Eutectic Die Attach:

- A. An 80/20 Au/Sn preform is recommended with a work surface temperature of approximately 255°C and a tool temperature of 265°C. When hot 90/5 nitrogen/hydrogen gas is applied, solder temperature should be approximately 290° C.
- B. DO NOT expose the MAAM28000 to a temperature greater than 320°C for more than 20 seconds. No more than 3 seconds of scrubbing should be required for attachment.

#### Epoxy Die Attach:

- A. Electrically conductive epoxy is required.
- B. Apply a minimum amount of epoxy and place the MAAM28000 into position. A thin epoxy fillet should be visible around the perimeter of the die.
- Cure epoxy per manufacturer's recommended schedule.

#### **Bonding**

- A. Ball or wedge bond with 1.0 mil diameter gold wire of 3.0 mil x 0.5 mil ribbon. Thermosonic bonding with a nominal stage temperature of 150°C and a ball bonding force of 40 to 50 grams or wedge bonding force of 18 to 22 grams is recommended. Ultrasonic energy and time should be adjusted to the minimum levels necessary to achieve reliable bonds.
- B. Bonds should be started on the die and terminated on the package.
- C. Bonding pads are 4.0 x 4.0 mils minimum.